CPH6350

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P-Channel Power MOSFET -30V, -6A, 43mΩ, Single CPH6

Features

- 4V drive
- · Low ON-resistance
- · Protection diode in

Specifications

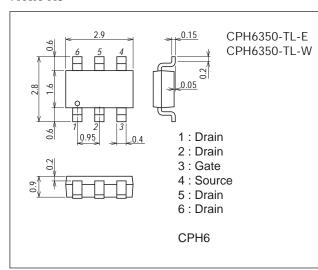
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		-30	V
Gate to Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		-6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-24	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

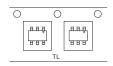
unit : mm (typ) 7018A-003



Ordering & Package Information

9	9			
Device	Package	Shipping	memo	
CPH6350-TL-E	CPH6 SC-74, SOT-26, SOT-457	3,000pcs./ reel	Pb-Free	
CPH6350-TL-W	CPH6 SC-74, SOT-26, SOT-457	3,000pcs./ reel	Pb-Free and Halogen Free	

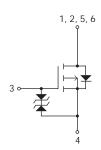
Packing Type: TL



Marking



Electrical Connection

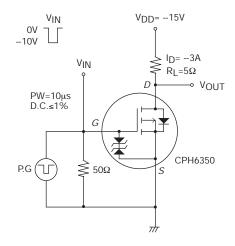


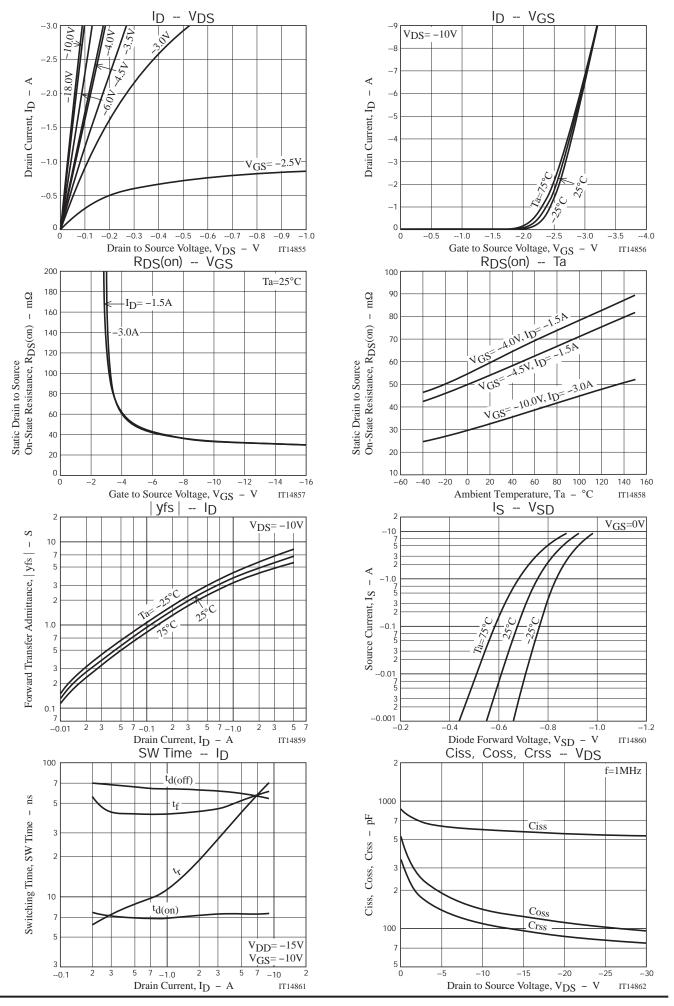
CPH6350

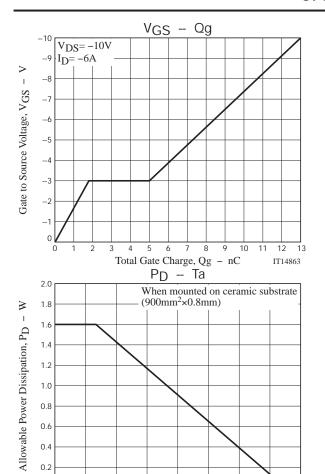
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-3A		5.4		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-3A, V _G S=-10V		33	43	mΩ
	R _{DS} (on)2	I _D =-1.5A, V _G S=-4.5V		58	82	mΩ
	R _{DS} (on)3	I _D =-1.5A, V _G S=-4V		61	86	mΩ
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		600		pF
Output Capacitance	Coss			145		pF
Reverse Transfer Capacitance	Crss			110		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		7.4		ns
Rise Time	t _r			27		ns
Turn-OFF Delay Time	td(off)			62		ns
Fall Time	tf			45		ns
Total Gate Charge	Qg	V _{DS} =-15V, V _{GS} =-10V, I _D =-6A		13		nC
Gate to Source Charge	Qgs			1.8		nC
Gate to Drain "Miller" Charge	Qgd			3.2		nC
Diode Forward Voltage	V _{SD}	IS=-6A, VGS=0V		-0.87	-1.2	V

Switching Time Test Circuit







80

Ambient Temperature, Ta - °C

100

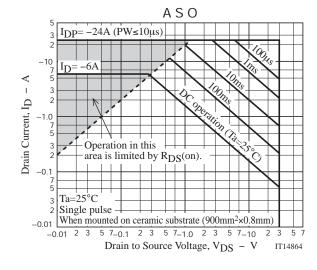
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160

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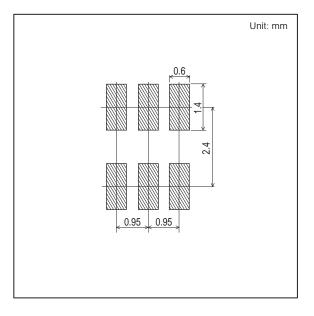


Outline Drawing

CPH6350-TL-E, CPH6350-TL-W

Mass (g) Unit 0.015 For reference mm 0. 15^{+0. 1}_{-0. 05} 2. 9±0. 1 0.6±0.1 A 0. 2±0.1 [*1][*1] 0. 05±0.05 2, 8±0, 15 . 6±0. 1 [*1] - \$ 0.95 0. 6±0. 1 PIN#1 0.05 \$ *1:Lot indication

Land Pattern Example



Note on usage: Since the CPH6350 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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